

SILICON PHOTODIODE VTP8740BTRH

FEATURES

- Surface mount package
- Low capacitance
- Fast response
- High shunt impedance
- Tape & reel supplied

PRODUCT DESCRIPTION

This planar silicon photodiode features a lensed, water clear epoxy package suitable for surface mount assembly in a "back mounted" (lens up) orientation.

These photodiodes exhibit performance charac - teristics which make them suitable for a wide range of near-IR sensing applications. Devices are shipped taped & reeled on a 24 mm embossed carrier.

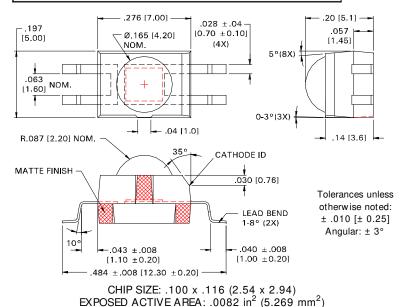
ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

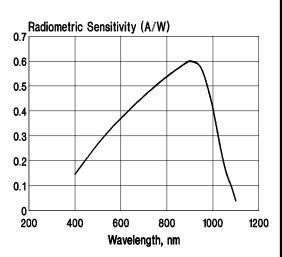
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
SHORT CIRCUIT CURRENT @ 100 fc, 2850 K	Isc	75	90		μΑ
DARK CURRENT @ V _R = 10 V	ID			20	nA
SHUNT RESISTANCE @ H = 0, V = 10 mV	Rsh		0.25		GΩ
JUNCTION CAPACITANCE @ V _R = 3 V	CJ			50	pF
OPEN CIRCUIT VOLTAGE @ 100 fc, 2850 K	Voc	325			mV
ANGULAR RESPONSE (50% RESPONSE POINT)	θ _{1/2}		±42		Degrees

PACKAGE DIMENSIONS inch (mm)

RoHS Compliant







TYPICAL SPECTRAL RESPONSE

VIP8/40BIRDS Rev. A (

GENERAL CHARACTERISTICS

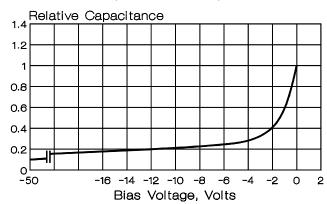
PARAMETER	SYMBOL	TYPICAL RATING	UNITS
PEAK SPECTRAL RESPONSE @ 25°C	λ_{P}	925	nm
RADIOMETRIC SENSITIVITY @ PEAK, 25°C	S _{RPK}	0.6	A / W
NOISE EQUIVALENT POWER	NEP	2.0 x 10 ⁻¹³	W/ √Hz
SPECIFIC DETECTIVITY	D*	1.2 x 10 ¹²	cm √Hz /W
TEMPERATURE COEFFICIENT SHORT CIRCUIT CURRENT @ 2850 K SOURCE OPEN CIRCUIT VOLTAGE @ 2850 K SOURCE DARK CURRENT	TC Isc TC Voc TC I _D	+0.22 - 2.0 +15.0	%/°C mV/ C %/°C

ABSOLUTE MAXIMUM RATINGS

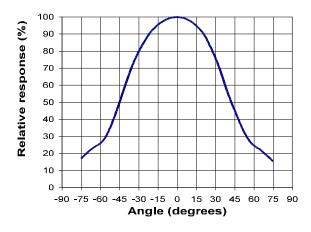
PARAMETER	SYMBOL	RATING	UNITS
TEMPERATURE RANGE OPERATING AND STORAGE	T_{AMB}	– 40 to +85	°C
LEAD SOLDER TEMPERATURE (1.6 mm FROM CASE, 5 SECONDS MAX.)	TLS	260°	°C
BREAKDOWN VOLTAGE @ 25°C	V_{BR}	33	Volts
POWER DISSIPATION	P_{D}	150	mW

TYPICAL CHARACTERISTIC CURVES

RELATIVE JUNCTION CAPACITANCE vs BIAS VOLTAGE (REFERRED TO ZERO BIAS)



ANGULAR RESPONSE



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